RoHS

COMPLIANT



## Vishay General Semiconductor

## Surface Mount Glass Passivated Ultrafast Rectifier



20 A

75 ns

15 mJ

150 °C

WWW.DZSC.CO

\* Glass-plastic encapsulation technique is covered by patent No. 3,996,602, brazed-lead assembly by Patent No. 3,930,306 and lead forming by Patent No. 5,151,846

 $I_{FSM}$ 

 $t_{rr}$ 

 $\mathsf{E}_\mathsf{AS}$ 

T<sub>.I</sub> max.

# PRIMARY CHARACTERISTICS I<sub>F(AV)</sub> 1.0 A V<sub>RRM</sub> 1300 V

#### **FEATURES**

- Cavity-free glass-passivated junction
- Ideal for automated placement
- Ultrafast reverse recovery time
- · Low switching losses, high efficiency
- Low switching losses, high emolene
- Avalanche surge energy capability
- Meets environmental standard MIL-S-19500
- Meets MSL level 1, per J-STD-020, LF maximum peak of 250 °C
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

#### **TYPICAL APPLICATIONS**

For use in high voltage rectification of photoflash application.

#### **MECHANICAL DATA**

Case: DO-214BA, molded plastic over glass body

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: Color band denotes cathode end

MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)				
PARAMETER	SYMBOL	EGF1T	UNIT	
Device marking code	BV/8 5 P	ET		
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	1300	V	
Maximum RMS voltage	$V_{RMS}$	910	V	
Maximum DC blocking	$V_{DC}$	1300	V	
Maximum average forward rectified current	$I_{F(AV)}$	1.0	Α	
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I <sub>FSM</sub>	20	А	
Non-repetitive avalanche energy at $T_A = 25$ °C, $I_{AS} = 1$ A, L = 30 mH	E <sub>AS</sub>	15	mJ	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to + 150	°C	

# EGF1T

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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)					
PARAMETER	TEST C	ONDITIONS	SYMBOL	EGF1T	UNIT
Maximum instantaneous forward voltage (1)	1.0 A	T <sub>J</sub> = 25 °C	V <sub>F</sub>	3.0	V
Maximum DC reverse current (2)	V <sub>RM</sub>	T <sub>J</sub> = 25 °C T <sub>J</sub> = 125 °C	I <sub>R</sub>	5.0 50	μΑ
Typical reverse recovery time	I <sub>F</sub> = 0.5 A, I <sub>R</sub> =1.0 A, I <sub>rr</sub> = 0.25 A		t <sub>rr</sub>	75	ns
Typical junction capacitance	4.0 V, 1 M	lHz	CJ	8.0	pF

#### Notes:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)				
PARAMETER	SYMBOL	EGF1T	UNIT	
Typical thermal resistance <sup>(1)</sup>	${\sf R}_{ heta \sf JA} \ {\sf R}_{ heta \sf JL}$	50 20	°C/W	

#### Note:

(1) Thermal resistance from junction to ambient and from junction to lead, P.C.B. mounted on 0.95 x 0.95" (24 x 24 mm) copper pad areas

ORDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
EGF1T-E3/67A	0.104	67A	1500	7" diameter plastic tape and reel		
EGF1T-E3/5CA	0.104	5CA	6500	13" diameter plastic tape and reel		
EGF1THE3/67A (1)	0.104	67A	1500	7" diameter plastic tape and reel		
EGF1THE3/5CA (1)	0.104	5CA	6500	13" diameter plastic tape and reel		

#### Note:

(1) Automotive grade AEC Q101 qualified

#### **RATINGS AND CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25 °C unless otherwise noted)

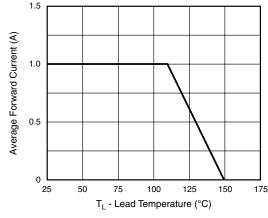


Figure 1. Maximum Forward Current Derating Curve

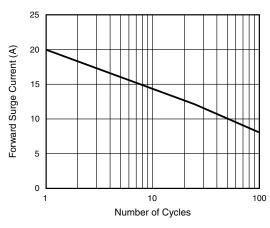


Figure 2. Maximum Non-Repetitive Forward Surge Current



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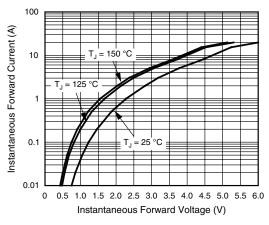


Figure 3. Typical Instantaneous Forward Characteristics

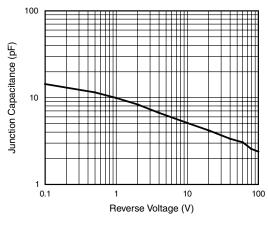


Figure 5. Typical Junction Capacitance Per Leg

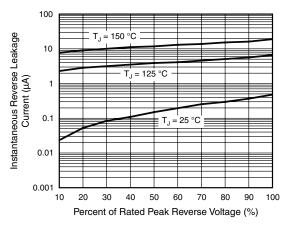


Figure 4. Typical Reverse Leakage Characteristics

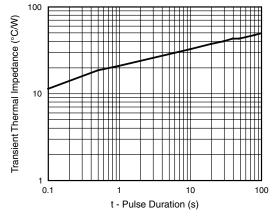


Figure 6. Typical Transient Thermal Impedance

#### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)

#### DO-214BA (GF1) Cathode Band **Mounting Pad Layout** 0.066 (1.68) 0.076 (1.93) 0.066 (1.68) MAX. 0.040 (1.02) MIN. 0.187 (4.75) 0.167 (4.24) 0.015 (0.38) 0.0065 (0.17) 0.060 (1.52) MIN. 0.118 (3.00) 0.108 (2.74) 0.098 (2.49) 0.100 (2.54) 0.220 (5.58) REF. ↑ 0.006 (0.152) TYP 0.114 (2.90) 0.060 (1.52) 0.094 (2.39) 0.030 (0.76) 0.226 (5.74) 0.196 (4.98)



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